



In re Application of:

Loucas Tsakalakos et al.

Serial No.:

10/722,700

Filed:

November 25, 2003

For:

ELONGATED NANO-

STRUCTURES AND RELATED

DEVICES

§ § §

§

§ §

§

Group Art Unit:

1754

Examiner:

Rebecca M. Stadler

Atty. Docket:

139081-1/SWA

GERD:0662

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 CERTIFICATE OF MAILING 37 C.F.R. 1.8

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date below;

December 11, 2006

Date

Táit R. Swanson

(

Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§ 1.97(c) AND 1.98

In compliance with the duty of disclosure under 37 C.F.R. § 1.56(a), it is respectfully requested that this Information Disclosure Statement be entered and that the listed references be considered by the Examiner and made of record. Applicants note that, due to recent amendments to 37 C.F.R. § 1.98(a), copies of the listed domestic references are no longer required to be submitted to the Examiner.

In accordance with 37 C.F.R. § 1.97, this Information Disclosure Statement is not to be construed as a representation that a search has been made, as an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 C.F.R. §1.56(b), or as a representation that no other possibly material information, as defined in 37 C.F.R. § 1.56(b), exists.

12/19/2006 ZJUHAR1 00000023 070868 10722700 01 FC:1806 180.00 DA

Serial no. 10/722,700 Information Disclosure Statement Page 2

Furthermore, the references listed on the attached PTO/SB/08 Forms are not to be construed as an admission that these references qualify as prior art as to the above-referenced application or any related application. Rather, these references are being presented for the Examiner's consideration without prejudice to the right to demonstrate that any of these references do not qualify as prior art should the Examiner choose to apply any of these references.

The following information is listed on the attached PTO/SB/08 Forms in accordance with 37 C.F.R. §1.98. Any explanation of non-English language documents contained in this Information Disclosure Statement is believed to constitute a concise explanation of the relevance of the listed reference as it is presently understood by the individual designated in § 1.56(c) most knowledgeable about the content of the listed reference, in accordance with 37 C.F.R. § 1.98(a)(3).

In accordance with 37 C.F.R. §1.97(c) a fee of \$180.00 is due for the present Information Disclosure Statement. The Commissioner is authorized the requisite fee, and any additional fee which may be required, to Deposit Account No. 07-0868; Order No. 139081-1/SWA (GERD:0662).

Respectfully submitted,

Date: December 11, 2006

Tait R. Swanson Reg. No. 48,226

FLETCHER YODER

P.O. Box 692289

Houston, TX 77269-2289

(281) 970-4545

PTO/SB/08A (09-06) Approved for use through 03/31/2007. OMB 0651-0031

·im.,

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction act of 1995, no per ons are required to respond to a collection of information unless it contains a valid OMB control number. Substitute for form 1449/PTO Complete if Known INFORMATION DISCLOSURE Application Number 10/722,700 STATEMENT BY APPLICANT November 25, 2003 Filing Date First Named Inventor Loucas Tsakalakos et al. (Use as many sheets as necessary) Art Unit **Examiner Name** Rebecca M. Stadler **Attorney Docket Number** 139081-1/SWA (GERD:0662) Sheet of

DEC 18 2006

			U.S.	PATENT DOC	CUMENTS	
Examiner Initials*	Cite No. ¹	Nur	Document Number mber-Kind Code ^{2 (if known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	US-	2003205966	11/06/2003	Chen Lai-Cheng et al.	
	A2	US-	2003087511	05/08/2003	Hidaka Kishio et al.	
	A3	US-	2003030356	02/13/2003	Fran Yui-Shin et al.	
	A4	US-	5,314,569	05/24/1994	Pribat et al.	
	A5	US-				
	A6	US-				
	A7	US-				
	A8	US-				
	A9	US-				
	A10	US-				
	A11	US-				
	A12	US-				
	A13	US-				
	A14	US-				
	A15	US-				
	A16	US-		1		
-	A17	US-				
<u> </u>	A18	US-				2
	A19	US-				

Examiner Initials*	Cite	Foreign Patent Document	Publication	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages	
	No.1	Country Code ³⁻ Number ⁴⁻ Kind Code ^{5(if known)}	Date MM-DD-YYYY	Applicant of Cited Document	or Relevant Figures	T ⁶
	B1	WO03048040	06/12/2003	Thales		
	B2	WO03025966	03/27/2003	Thales		
	В3	WO03018466	03/06/2003	SI Diamond Tech		• •
	B4					
	B5					• •
	B6					•

Examiner	Date
Signature	Considered

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-9199 (1-800-786-9199) and select option 2.

PTO/SB08B (09-06)

Approved for use through 03/31/2007. OMB 0651-0031 ···

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1440/DTO Substitute for form 1449/PTO Complete if Known **INFORMATION DISCLOSURE Application Number** 10/722,700 STATEMENT BY APPLICANT November 25, 2003 Filing Date First Named Inventor Loucas Tsakalakos et al. (Use as many sheets as necessary) Art Unit 1754 **Examiner Name** Rebecca M. Stadler Sheet **Attorney Docket Number** 139081-1/SWA (GERD:0662)

		NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
	C1	TSAKALAKOS, LOUCAS ET AL.: "Mo2C Nanowires and Ribbons on Si Via Two-Step Vapor Phase Growth," Proceedings of the 3 rd ASME Integrated Nanosystems Conference-Design, Synthesis, and Applications; 2004, pages 129-130.	i i Li, Ingelje Li i	
	C2	SHAJAHAN MD. ET AL.: "Effect of Chemical Vapor Deposition Energy Sources on the Structure of SiC Prepared by Carbon Nanotubes-Confined Reaction," Journal of Vacuum Science & Technology B: Microelectronics Processing and Phenomena, American Vacuum Society, New York, NY, US, vol. 21, no. 3, May 2003, pages 1149-1156.	10) 29 * 10 k	
	С3	ING-CHI LEU ET AL.: "Nucleation Behavior of Silicon Carbide Whiskers Grown by Chemical Vapor Deposition," Journal of Crystal Growth Elsevier Netherlands, vol. 236, no. 1-3, 1 March 2002, pages 171-175.		
• •	C4	FUKUNAGA, AKIHIKO ET AL.: "Synthesis, Structure, and Superconducting Properties of NbC Nanorods and Nanoparticles," Materials Transactions, JIM, Feb. 1999 Japan Inst. of Metals, Sendai, Japan, vol. 40, no. 2, February 1999, pages 118-122.		
	C5	LIEBER, CHARLES M. ET AL.: "Growth and Structure of Carbide Nanorods," Materials Research Society Symposium Proceedings; Covalent Ceramics III – Science and Technology of Non-Oxides; Materials Research Society, Pittsburgh, PA, USA, vol. 410, 27 November 1995, pages 103-111.		
	C6	KATO ET AL.: "Formation of Micro SiC Tubes by the Carburization of Si Whiskers," Journal of the American Ceramic Society USA, vol. 63, no. 3-4, March 1980, page 236.		
			;;	
			i	
			-	